

Sep 23 2003

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Substitute for form 1449/PTO

Complete if Known  
Application Number NEW APPLICATION  
Filing Date HEREWITH  
First Named Inventor Milan R. Kokta  
Attorney Docket Number 1035-BI3918-CIP

Sheet 1 of 3  
(use as many sheets as necessary)

### U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No.1	U.S. Patent Document Number	Kind Code <sup>z</sup> (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
QW	AA	3,655,439		SEITER	04/11/1972	—
	AB	3,658,586		WANG	04/25/1972	—
	AC	3,796,597		V.R. PORTER, et al.	03/12/1974	—
	AD	4,177,321		NISHIZAWA	12/04/1979	—
	AE	5,741,724		RAMDANI, et al.	04/21/1998	—
	AF	5,850,410		KURAMATA	12/15/1998	—
	AG	5,530,267		BRANDLE, JR., et al.	06/25/1996	—
	AH	6,104,529		BRANDLE, JR., et al.	08/15/2000	—
	AI	3,883,313		CULLEN, et al.	05/13/1975	—
	AJ	5,802,083		BIRNBAUM	09/01/1998	—
WV	AK	2003/0007520	A1	KOKTA, et al.	01/09/2003	—

### FOREIGN PATENT DOCUMENTS

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QW	AL	EP	0 148 656		AUZEL, et al.	11/16/1984	—	<input type="checkbox"/>
	AM						—	<input type="checkbox"/>

### PUBLICATIONS

Examiner Initials *	Cite No.1	Title of Publication	Date of Publication of Cited Document MM-DD-YYYY
QW	AV	YUMASHEV K.V., et al., "Co <sup>2+</sup> -doped spinels saturable absorber Q-switches for 1.3-1.6 μm solid state lasers", OSA TRENDS IN OPTICS AND PHOTONICS. ADVANCED SOLID STATE LASERS., Vol. 34, pp. 236-239, 2000. XP008017966	—
	AW	YUMASHEV, K.V., et al., "Passive Q-switching of 1.34-m neodymium laser using Co <sup>2+</sup> :LiGa <sub>5</sub> O <sub>8</sub> and Co <sup>2+</sup> :MgAl <sub>2</sub> O <sub>4</sub> ", CONFERENCE DIGEST, 2000, 1 page. XP002242959	—
	AX	OKTYABRSKY, S., et al., "Crystal structure and defects in nitrogen-deficient GaN", MRS Internet J. Nitride Semicond. Res, G6.43, pp. 1-6, 1999.	—
	AY	KLEBER, W., et al., "Zur Epitaxie von Galliumnitrid auf nichtstochiometrischem Spinnell im System GaCl/NH <sub>3</sub> /He", CRYSTAL RESEARCH AND TECHNOLOGY, Vol. 10, No. 7, pp. 747-758, 1975. (English Abstract)	—
WV	AZ	SEIFERT, A., "Nachweis von Stäbelfehlern in GaN-Epitaxieschichten mittels Elektronenbeugung", CRYSTAL RESEARCH AND TECHNOLOGY, Vol. 10, No. 7, pp. 741-746 1975. (English Abstract)	—
Examiner Signature	James Vannucci	Date Considered	7-12-05

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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First Name Inventor Milan R. Kokta

Attorney Docket Number 1035-BI3918-CIP

Sheet 2 of 3

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W	BA	6,533,874	B1	VAUDO, et al.	03/18/2003	—
↓	BB	4,627,064		AUZEL, et al.	12/02/1986	—
↓	BC	4,000,977		FALCKENBERG	01/04/1977	—
BD						
BE						
BF						
BG						
BH						
BI						
BJ						
BK						

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	BL						<input type="checkbox"/>
	BM						<input type="checkbox"/>

## PUBLICATIONS

Examiner Initials *	Cite No.1	Title of Publication	Date of Publication of Cited Document MM-DD-YYYY
JW	BW	OHSATO, H., et al., "Epitaxial orientation and a growth model of (0 0 • 1) GaN thin film on (1 1 1) spinel substrate", JOURNAL OF CRYSTAL GROWTH, Vol. 189/190, pp. 202-207, 1998.	—
↑	BX	YANG, H. -F., et al., "Microstructure evolution of GaN buffer layer on MgAl <sub>2</sub> O <sub>4</sub> substrate", JOURNAL OF CRYSTAL GROWTH, Vol. 193, pp. 478-483, 1998.	—
↑	BY	DUAN, S., et al., "MOVPE growth of GaN and LED on (1 1 1) MgAl <sub>2</sub> O <sub>4</sub> ", JOURNAL OF CRYSTAL GROWTH, Vol. 189/190, pp. 197-201, 1998.	—
↓	BZ	SHELDON, R., et al., "Cation Disorder and Vacancy Distribution in Nonstoichiometric Magnesium Aluminate Spinel, MgO • Al <sub>2</sub> O <sub>3</sub> ", J. AM. CERAM. SOC., Vol. 82, No. 12, pp. 3293-3298, 1999.	—
Examiner Signature	James Varnuccio		Date Considered 7-12-65

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First Named Inventor Milan R. K. Kta

Attorney Docket Number 1035-BI3918-CIP

Sheet 3 of 3

(use as many sheets as necessary)

## PUBLICATIONS

Examiner Initials *	Cite No.1	Title of Publication	Date of Publication of Cited Document MM-DD-YYYY
QW	AAA	KULESHOV, N.V., et al. "Co-doped spinels: promising materials for solid state lasers", LONGER WAVELENGTH LASERS AND APPLICATIONS, Vol. 2138, pp. 175-182, 1994. XP008017848	—
1	AAB	KULESHOV, N.V., et al., "Absorption and luminescence of tetrahedral Co <sup>2+</sup> ion in MgAl <sub>2</sub> O <sub>4</sub> ", Vol. 55, no. 5-6, pp. 265-269, 1993. XP008017849	—
1	AAC	NIKISHIN, S.A., et al., "Gas source molecular beam epitaxy of GaN with hydrazine on spinel substrates", APPLIED PHYSICS LETTERS, Vol. 72, No. 19, pp. 2361-2363, 1998. XP000755963	—
	AAD	HAISMA, et al., "Lattice constant adaptable crystallographics", JOURNAL OF CRYSTAL GROWTH, Vol. 102, pp. 979-993, 1990. XP002250056	—
	AAE	TAMURA, K., et al., "Epitaxial growth of ZnO film on lattice-matched ScAlMgO <sub>4</sub> (0001) substrates", JOURNAL OF CRYSTAL GROWTH, Vol. 214-215, pp. 59-62, 2000. XP004200964	—
	AAF	WYON, et al., "Czochralski growth and optical properties of magnesium-aluminum spinel doped with nickel", JOURNAL OF CRYSTAL GROWTH, Vol. 79, pp. 710-713, 1986. XP002250057	—
	AAG	TSUCHIYA, T., et al. "Epitaxial growth of InN films on MgAl <sub>2</sub> O <sub>4</sub> (1 1 1) substrates", JOURNAL OF CRYSTAL GROWTH, Vol. 220, pp. 185-190, 2000.	—
E	AAH	KURAMATA, Akito, et al., "High-quality GaN epitaxial layer grown by metalorganic vapor phase epitaxy on (111) MgAl <sub>2</sub> O <sub>4</sub> substrate", APPL. PHYS. LETT., Vol. 67, No. 17, pp. 2521-2523, 1995.	—
	AAI	MITCHELL, T., "Dislocations and Mechanical Properties of MgO- MgAl <sub>2</sub> O <sub>3</sub> spinel single crystals", J. AM. CERAM. SOC., Vol. 82, No. 12, pp. 3305-3316, 1999.	—
	AAJ	HELLMAN, E., "Exotic and Mundane substrates for gallium nitride heteroepitaxy", BELL LABORATORIES, THC2, Murray Hill, NJ.	—
	AAK	KRUGER, M.B., et al., "Equation of state of MgAl <sub>2</sub> O <sub>4</sub> spinel to 65 GPa", THE AMERICAN PHYSICAL SOCIETY, Vol. 56, No. 1, pp. 1-4, 1997.	—
	AAL	KURAMATA, A., et al., "Properties of GaN epitaxial layer grown on (111) MgAl <sub>2</sub> O <sub>4</sub> substrate", SOLID-STATE ELECTRONICS, Vol. 41, No. 2, pp. 251-254, 1997.	—
↓	AAM	GRITSYNA, V., et al., "Structure and Electronic states of defects in spinel of different compositions MgO : n MgAl <sub>2</sub> O <sub>3</sub> : Me", J. AM. CERAM. SOC. Vol. 82, No. 1, pp. 3365-3373, 1999.	—

Examiner Signature

Jamer Vannucci

Date Considered

7-12-05

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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Substitute for form 1449A/PTO

Sheet 1 of 1  
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Complete if Known  
Application Number 10/669,145  
Filing Date September 23, 2003  
First Name of Inventor Milan R. Kokta  
Group Art Unit  
Examiner Name  
Attorney Docket Number 1035-BI3918-CIP

## U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. 1	U.S. Patent Document Number	Kind Code 2 (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
W	AA	4,493,720		Gauthier, et al.	01/15/1995	—
	AB	5,644,400		Mundt	07/01/1997	—
	AC	5,768,335		Shahid	06/16/1998	—
	AD	5,825,913		Rostami, et al.	10/20/1998	—
	AE	5,822,213		Huynh	10/13/1998	—
	AF	6,021,380		Fredriksen, et al.	02/01/2000	—
	AG	4,819,167		Cheng, et al.	04/04/1989	—
	AH					
	AI					
	AJ					

## FOREIGN PATENT DOCUMENTS

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	AK						<input type="checkbox"/>
	AL						<input type="checkbox"/>
	AM						<input type="checkbox"/>
	AN						<input type="checkbox"/>
	AO						<input type="checkbox"/>

## PUBLICATIONS

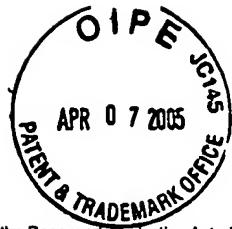
Examiner Initials *	Cite No. 1	Title of Publication	Date of Publication of Cited Document MM-DD-YYYY
	AW		
	AX		
	AY		
	AZ		

Examiner Signature	<i>James Vannuccini</i>	Date Considered	7-12-05
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PTO/SB/08A (08-03)

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INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

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Sheet 1

of 3

## Complete if Known

Application Number	10/669,145
Filing Date	September 23, 2003
First Named Inventor	Milan R. Kokta
Art Unit	2828
Examiner Name	Minsun Oh Harvey

Attorney Docket Number 1035-BI3918-CIP

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✓	AA	US- 3,625,868	12/07/1971	Grabmaier et al.	—
	AB	US- 3,736,158	05/29/1973	Cullen et al.	—
	AC	US- 3,816,906	06/18/1974	Falckenberg	—
	AD	US- 3,883,313	05/13/1975	Cullen et al.	—
	AE	US- 3,885,978	05/27/1975	Doi et al.	—
	AF	US- 3,990,902	11/09/1976	Nishizawa, et al.	—
	AG	US- 3,950,504	04/13/1976	Belding et al.	—
	AH	US- 4,370,739	01/25/1983	Wang et al.	—
	AI	US- 4,755,314	07/05/1988	Sakaguchi et al.	—
	AJ	US- 5,138,298	08/11/1992	Shino	—
	AK	US- 5,850,410	12/15/1998	Kuramata	—
	AL	US- 6,533,874 B1	03/18/2003	Vaudo et al.	—
	AM	US- 2003/0188678 A1	10/09/2003	Kokta et al.	—
	AN	US- 6,839,362 B2	01/05/2005	Kokta et al.	—
✓	AO	US- 6,844,084 B2	01/18/2005	Kokta et al.	—
	AP	US- 3,424,955	01/28/1969	Seiter et al.	—
	AQ	US-			
	AR	US-			
	AS	US-			

## FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T <sup>6</sup>
✓	AT	FR 1,471,976	03/24/1966	Siemens Aktiengesellsc.	Corr. 3,424,955	
	AU	JP 11-157997	06/15/1999	Kyocera Corporation	Abstract Only	
	AV	JP 09-278595	10/28/1997	Sumitomo Elect. Ind. Ltd.	Abstract Only	
	AW	JP 62-188325	08/17/1987	Sumitomo Elect. Ind. Ltd.	Abstract Only	
	AX	JP 58-211736	12/09/1983	Toshiba Corporation	Abstract Only	
	AY	JP 07-307316	11/21/1995	Sumitomo Elect. Ind. Ltd.	Abstract Only	

Examiner Signature

*Jane Vanucci*

Date Considered

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Sheet 2of 3**Complete if Known**

Application Number	10/669,145
Filing Date	September 23, 2003
First Named Inventor	Milan R. Kokta
Art Unit	2828
Examiner Name	Minsun Oh Harvey

Attorney Docket Number 1035-BI3918-CIP

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	BB	US-			
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	BD	US-			
	BE	US-			
	BF	US-			
	BG	US-			
	BH	US-			
	BI	US-			
	BJ	US-			
	BK	US-			
	BL	US-			
	BM	US-			
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	BO	US-			
	BP	US-			
	BQ	US-			
	BR	US-			
	BS	US-			

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		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
gw	BT	EP 0 762 930 B1	07/12/2000	BP Amoco Corporation	—	
gw	BU	EP 0 263 171 B1	11/25/1992	UOP	—	
gw	BV	WO 01/99155 A2	12/27/2001	Nichia Corporation	—	
gw	BW	WO 02/95887 A2	11/28/2002	SG Ceramics & Plastics Inc.	—	
	BX					
	BY					

Examiner Signature

*Jeanne Vannucci*

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		Examiner Name	Minsun Oh Harvey
Sheet	3	of	3
		Attorney Docket Number	
		1035-BI3918-CIP	

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
gw	CA	Gieß et al., "Growth of Single Crystal MgGa <sub>2</sub> O <sub>4</sub> Spinel", IBM TECHNICAL DISCLOSURE BULLETIN, Vol. 15, no. 1, June 1972, pgs 151-152, XP-002315746.	-
	CB	Anon., "Spinel Crystals for Electronic Devices", MANUFACTURING TECHNOLOGY NOTE, Vol. NTN-77, no. 0735, April 1977, XP-002315747.	-
	CC	Grabmaier et al., "Czochralski Growth of Magnesium-Aluminum Spinel", J. AMERICAN CERAMIC SOCIETY, Vol. 51, no. 6, June 1968, pgs 355-356, XP-002315185.	-
	CD	Wyon et al., "Czochralski Growth and Optical Properties of Magnesium-Aluminum Spinel Doped with Nickel", JOURNAL OF CRYSTAL GROWTH, NORTH-HOLLAND PUBLISHING CO. AMSTERDAM, NL, Vol. 79, no. 1-3, part 2, 1986, pgs 710-713, XP-002250057.	-
	CE	Pinckney, L.R., "Transparent, high strain point spinel glass-ceramics", JOURNAL OF NON-CRYSTALLINE SOLIDS, Vol. 255, pp. 171-177, 1999.	-
	CF	Nakamura, S. "Current Status and Future Prospects of InGaN-Based Laser Diodes", ISAP INTERNATIONAL, Vol. 1, pgs. 5-17, 2000.	-
	CG	Kisailus D., et al., "Growth of Epitaxial GaN on LiGaO <sub>2</sub> Substrates Via a Reaction With Ammonia", J. MATER. RES., Vol. 16, no. 7, pgs 2077-2081, 2001.	-
	CH	Nakamura, S., et al., "InGaN MQW LDs Grown on MgAl <sub>2</sub> O <sub>4</sub> Substrates," In THE BLUE LASER DIODE, (NY: Springer-Verlag), pp. 233-243, 1997 (update included).	-
	CI	Mordoc, H., et al., "Large-band-gap SiC, III-V nitride, and II-vi ZnSe-based Semiconductor Device Technologies", J. APPL. PHYS., Vol. 76, no. 3, pgs 1363-1398, 1994.	-
	CJ		

Examiner Signature	<i>Jane Vannuccini</i>	Date Considered	7-12-05
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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet

1

of 1

**Complete if Known**

Application Number	10/669,145
Filing Date	September 23, 2003
First Named Inventor	Milan R. Kokta
Art Unit	2828
Examiner Name	Minsun Oh Harvey

Attorney Docket Number 1035-BI3918-CIP

<b>U. S. PATENT DOCUMENTS</b>					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
SW	A	US- 3,808,065	04-30-1974	Robinson, et al.	—
	B	US- 3,898,051	08-05-1975	Schmid	—
↓	C	US- 4,347,210	08-31-1982	Maguire, et al.	—
↓	D	US- 5,968,267	10-19-1999	Li	—
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
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	M	US-			
	N	US-			
	O	US-			
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<b>FOREIGN PATENT DOCUMENTS</b>					
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
T					—
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V					—
W					—
X					—
Y					—

Examiner Signature	James Vannucca	Date Considered	7-12-05
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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1

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**Complete if Known**

Application Number	10/669,145
Filing Date	September 23, 2003
First Named Inventor	Milan R. Kokta
Art Unit	4776 2828
Examiner Name	UNASSIGNED
Attorney Docket Number	1035-BI3918-CIP

**U. S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
QV	AA	US- 4,963,520	10/16/1990	Yoo, et al.	—
	AB	US- 5,982,796	11/09/1999	Kokta, et al.	—
	AC	US- 5,654,973	08/05/1997	Stultz, et al.	—
	AD	US- 5,557,624	09/17/1996	Stultz, et al.	—
	AE	US- 6,366,596	04/02/2002	Yin, et al.	—
	AF	US- 6,023,479	02/08/2000	Thony, et al.	—
	AG	US-			
	AH	US-			
	AI	US-			
	AJ	US-			
	AK	US-			
	AL	US-			
	AM	US-			
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	AQ	US-			
	AR	US-			
	AS	US-			

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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
AT						
AU						
AV						
AW						
AX						
AY						

Examiner Signature

James Vannucci

Date Considered

7-12-05

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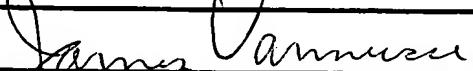
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Substitute for form 1449/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(Use as many sheets as necessary)</i>		<b>Complete if Known</b>	
		Application Number	10/669,145
		Filing Date	September 23, 2003
		First Named Inventor	Milan R. Kokta
		Art Unit	1775-2828
Examiner Name	UNASSIGNED		
Sheet <b>2</b>	of <b>3</b>	Attorney Docket Number	1035-BI3918-CIP

<b>NON PATENT LITERATURE DOCUMENTS</b>				
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T <sup>2</sup>
W	BA	Efimov, A.N., et al., "On an Unusual Azimuthal Orientation Relationship in the System Gallium Nitride Layer on Spinel Substrate", CRYSTALLOGRAPHY REPORTS, 45(2): 312-317 (2000).		-
	BB	Sun C.J., et al., "Mg-doped green light emitting diodes over cubic (1 1 1) MgAl2O4 substrate", APP. PHYS. LETT. 72(19): 2361-2363 (1998).		-
	BC	Efimov, A.N., et al., "Symmetry constraints and epitaxial growth on non-isomorphic substrate", THIN SOLID FILMS 260: 111-117 (1995).		-
	BD	George, T., et al., "Novel symmetry in the growth of gallium nitride on magnesium aluminate substrates", APPL. PHYS. LETT. 68(3): 337-339 (1996).		-
	BE	Sun C.J., et al., "Deposition of high quality wurtzite GaN films over cubic (1 1 1) MgAl2O4 substrates using low pressure and metalorganic chemical vapor deposition," APPL. PHYS. LETT. 68(8): 1129-1131 (1996).		-
	BF	Nakamura, S., et al., "Characteristics of InGaN multi-quantum-well-structure laser diodes," APPL. PHYS. LETT. 68(23): 3269-3271 (1996).		-
	BG	Khan, M.A., et al., "Cleaved cavity optically pumped InGaN-GaN laser grown on spinel substrates," APPL. PHYS. LETT. 69(16): 2418-2420 (1996).		-
	BH	Tempel, A., et al., "Nachweis von Stapelfehlern in GaN-Exitaxieschichten mittels Elektronenbeugung," KRISTALL UND TECHNIK 10(7): 741-746 (1975).		-
	BI	Tempel, A., et al., "Zur Epitaxie von Galliumnitrid auf nichtstoechiometrischem Spinell im System GaC1/NH3/He," KRISTALL UND TECHNIK 10(7): 747-758 (1975)		-
✓	BJ	K.V. Yumashev, "Saturable absorber Co <sup>2+</sup> : MgAl <sub>2</sub> O <sub>3</sub> crystal for Q switching of 1.34-μm Nd <sup>3+</sup> : YAlO <sub>3</sub> and 1.54-μm Er <sup>3+</sup> : glass lasers," APPLIED OPTICS 38(30): 6343-6346 (1999).		✓

Examiner Signature		Date Considered	7-12-05
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(Use as many sheets as necessary)</i>		Application Number	10/669,145
		Filing Date	September 23, 2003
		First Named Inventor	Milan R. Kokta
		Art Unit	1775- 2828
		Examiner Name	UNASSIGNED
Sheet	3	of	3
		Attorney Docket Number	1035-BI3918-CIP

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Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
JW	CA	Camargo, M.B., et al., "Co2+ Y3Sc2Ga3O12 (YSGG) Passive Q-Switch for Infared Erbium Lasers," submitted to LEOS in 1994.	-
/	CB	Mikhailov, V.P., et al., "Passive Q-switch performance at 1.3u (1.5u) and nonlinear spectroscopy of Co2+: MgAl2O4 and Co2+: LaMgAl11O9 cyrstals," OSA TOPS VOL. 26 Advanced Solid-State Lasers, pp. 317-324 (1999).	-
/	CC	Stulz, R.D., et al., "Diavalent Uranium and Cobalt Saturable Absorber Q-Switches at 1.5um," OSA Proceedings on Advanced Solid-State Lasers, 24:460-464 (1995).	-
/	CD	Birnbaum, M., et al., " Co2+: ZnSe Saturable Absorber Q-Switch for the 1.54 Um Er3+: Yb3+: Glass Laser," OSA TOPS Vol. 10 Advanced Solid State Lasers, pp. 148-151 (1997).	-
/	CE	Machida, H., et al., "difficulties encountered during the Czochralski growth of TiO2 single crystals," JOURNAL OF CYRSTAL GROWTH, 112: 835-837 (1997).	-
/	CF	Camargo, M.B., et al., "Broad-band 1.54 um Saturable Absorber Q-switch with Co2+, " submitted to ASSL in 1995.	-
✓	CG	Yumashev, K.V., et al., "Nonlinear spectroscopy and passive Q-switching operation of a Co2+: LaMgAl11O19 crystal," J. OPT. SOC. AM. B., 16(12): 2189-2194 (1999).	-
	CH		
	CI		
	CJ		

Examiner Signature	James Vannucci	Date Considered	7-12-05
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